NSN 5961-00-137-0812

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View Online at https://aerobasegroup.com/nsn/5961-00-137-0812

Inclosure Material:

Metal

Overall Length:

Between 0.300 inches and 0.405 inches

End Application:

Snavigation radio set; deep submergence systems; ticonderoga class cg (47); supruance class dd (963); nimitz class cvn; arleigh burke class ddg; oliver perry class ffg; tarawa class lha; emory s. Land class as; supply class aoe

Mounting Facility Quantity:

1

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 0.423 inches and 0.438 inches

Thread Size:

0.190 inches

Criticality Code Justification:

Feat

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

39.0 regulator voltage

Current Rating Per Characteristic:

1.20 amperes forward current, average pascal

Power Rating Per Characteristic:

10.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius case

Special Features:

Weapon system essential

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 tab, solder lug and 1 threaded stud

Specification Data:

81349-mil-s-19500/124 government specification

Shelf Life:

NI/o

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In	18	<i>(</i>)+	МЛО	201	ure:

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Demilitarization:

No

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